

In the Claims:

Please cancel claims 1 and 6 without prejudice or disclaimer.

Please amend claims 2-3 and 7-8, as follows:

Claim 1 (currently canceled)

Claim 2 (currently amended) ~~The gate structure method according to claim 4~~, wherein the etching prevention layer is titanium or titanium nitride.

Claim 3 (currently amended) A method for forming a gate electrode of high integration semiconductor device comprising the steps of:

sequentially depositing a gate oxide layer, a polysilicon layer, a tungsten nitride layer, a tungsten layer, and a nitride layer on the semiconductor substrate to form a resultant material structure on the semiconductor substrate;

depositing an etching prevention layer on the resultant structure; and
depositing an anti-reflection layer sequentially on the etching prevention layer resultant material;

forming a pattern by depositing a photoresist layer on the anti-reflection layer and executing a mask process;

etching the nitride layer, the tungsten layer and the tungsten nitride layer sequentially with an etching gas comprising fluorine; and

etching the etching prevention layer and the polysilicon layer with an etching gas comprising chlorine.

Claim 4 (original) The method for forming a gate according to claim 3, wherein the etching prevention layer has a thickness ranging from about 50 to about 1000Å.

Claim 5 (original) The method for forming a gate according to claim 3, wherein the etching gas comprising fluorine is selected from the group consisting of NF₃, SF₆ and CF₄ gases.

Claim 6 (currently canceled)

Claim 7 (currently amended) The ~~semiconductor device~~ method of claim 6 8, wherein the etching prevention layer is titanium or titanium nitride.

Claim 8 (currently amended) A method for forming a gate electrode of a high integration semiconductor device comprising the steps of:

providing a semiconductor substrate,

sequentially depositing a gate oxide layer, a polysilicon layer, a tungsten nitride layer, a tungsten layer and a nitride layer on the semiconductor substrate,

depositing an etching prevention layer on the nitride layer,

depositing an anti-reflection layer on the etching prevention layer;

forming a pattern by depositing a photoresist layer on the anti-reflection layer using a mask process,

etching the nitride layer, the tungsten layer and the tungsten nitride layer sequentially with an etching gas comprising fluorine, and

etching the etching prevention layer and the polysilicon layer with an etching gas comprising chlorine.

Claim 9 (original) The method of claim 8, wherein the etching prevention layer has a thickness ranging from about 50 to about 1000 Å.

Claim 10 (original) The method of claim 8, wherein the etching gas comprising fluorine is selected from the group consisting of NF₃, SF₆ and CF₄ gases.